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(71)Applicant : FUJI PHOTO FILM CO LTD

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(72)Inventor : MIZUTANI KAZUYOSHI  
YASUNAMI SHOICHIRO  
SHIRAKAWA KOJI  
TAKAHASHI AKIRA  
FUJIMORI TORU

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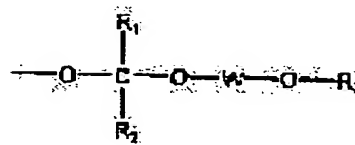
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(54) POSITIVE RESIST COMPOSITION FOR ELECTRON BEAM, X-RAY OR EUV

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a positive resist composition which improves the profile of a resist pattern and suppresses a variation of line width due to laying in a vacuum chamber.

SOLUTION: The positive resist composition for an electron beam, X-rays or EUV (extreme-ultraviolet radiation) comprises (a) a resin which has a structural unit containing an acid-decomposable group of formula (X) and is decomposed by the action of an acid to increase solubility in an alkali developer and (b) a compound which generates an acid upon irradiation with an actinic radiation. In formula (X), R1 and R2 may be the same or different and are each H or a 1-4C alkyl; W is a divalent organic group; and R3 is an alkyl which may have substituents and has 11-20 carbon atoms in total, an aryl which may have substituents and has 11-30 carbon atoms in total or an aralkyl which may have substituents and has 12-30 carbon atoms in total.



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